

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	23mΩ @ V <sub>GS</sub> = 10V	55A
	28mΩ @ V <sub>GS</sub> = 4.5V	48A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

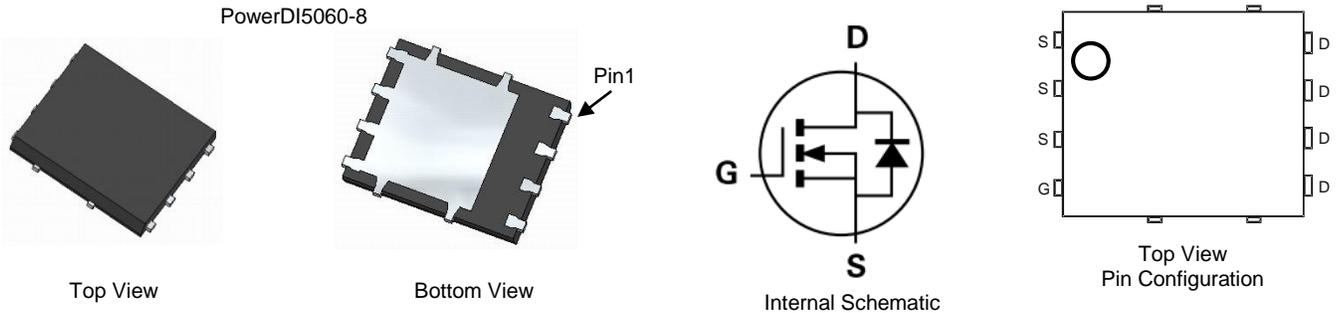
- Driving Solenoids
- Driving Relays
- Power Management Functions

## Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

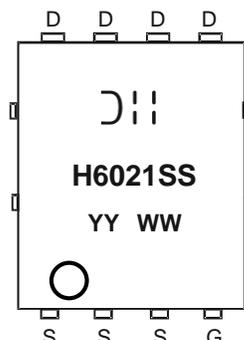


## Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH6021SPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



- D = Manufacturer’s Marking
- H6021SS = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Year (ex: 16 = 2016)
- WW = Week (01 to 53)

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**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 8)	I <sub>D</sub>	T <sub>C</sub> = +25°C	55
		T <sub>C</sub> = +100°C	39
Maximum Continuous Body Diode Forward Current (Note 8)	I <sub>S</sub>	55	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	88	A
Avalanche Current, L = 0.1mH (Note 9)	I <sub>AS</sub>	35	A
Avalanche Energy, L = 0.1mH (Note 9)	E <sub>AS</sub>	64	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	96	°C/W
Total Power Dissipation (Note 7)	P <sub>D</sub>	3.0	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	50	°C/W
Total Power Dissipation (Note 8)	P <sub>D</sub>	53	W
Thermal Resistance, Junction to Case (Note 8)	R <sub>θJC</sub>	1.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 10)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	µA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 10)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	12	23	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A
		-	18	28		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12A
Diode Forward Voltage	V <sub>SD</sub>	-	0.75	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 11)</b>						
Input Capacitance	C <sub>iss</sub>	-	1,016	-	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	-	153	-		
Reverse Transfer Capacitance	C <sub>riss</sub>	-	76.8	-		
Gate Resistance	R <sub>g</sub>	-	2.5	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	-	9.5	-	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	-	19.7	-		
Gate-Source Charge	Q <sub>gs</sub>	-	3.6	-		
Gate-Drain Charge	Q <sub>gd</sub>	-	4.8	-		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.2	-	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A, R <sub>g</sub> = 4.7Ω
Turn-On Rise Time	t <sub>R</sub>	-	13	-		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	27.5	-		
Turn-Off Fall Time	t <sub>F</sub>	-	15.3	-		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	20.8	-	ns	I <sub>F</sub> = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	13.9	-	nC	

- Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  8. Thermal resistance from junction to soldering point (on the exposed drain pad).
  9. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  10. Short duration pulse test used to minimize self-heating effect.
  11. Guaranteed by design. Not subject to product testing.

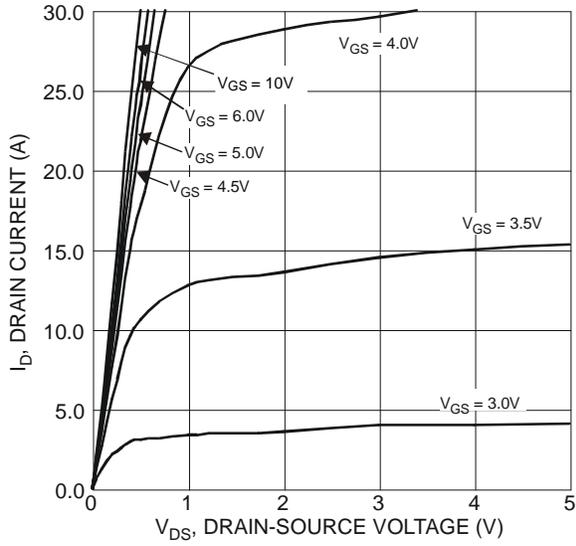


Figure 1 Typical Output Characteristics

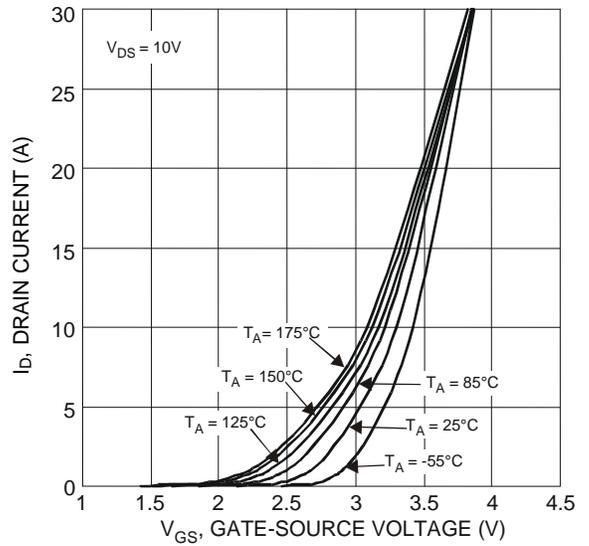


Figure 2 Typical Transfer Characteristics

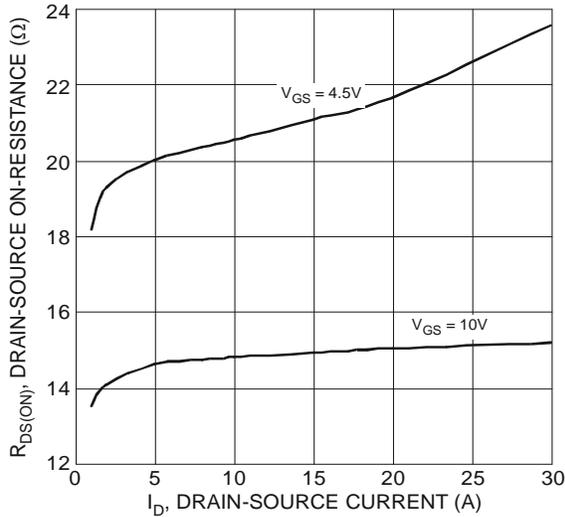


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

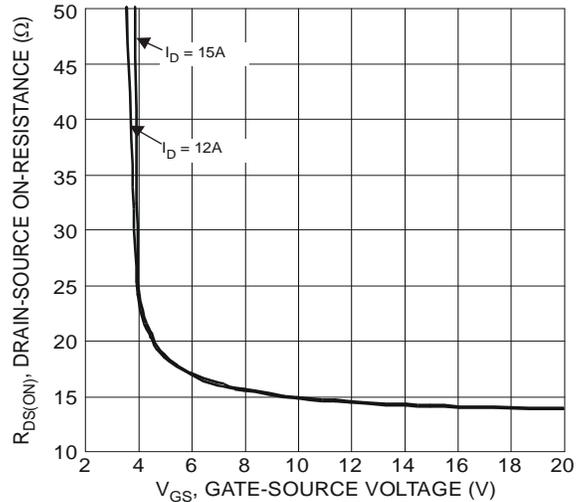


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

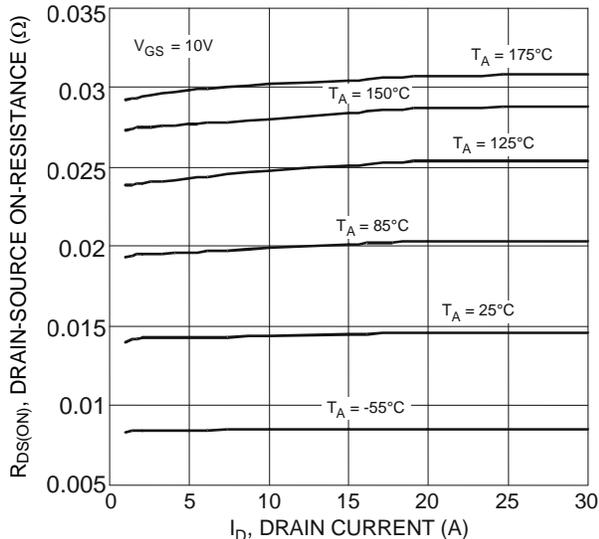


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

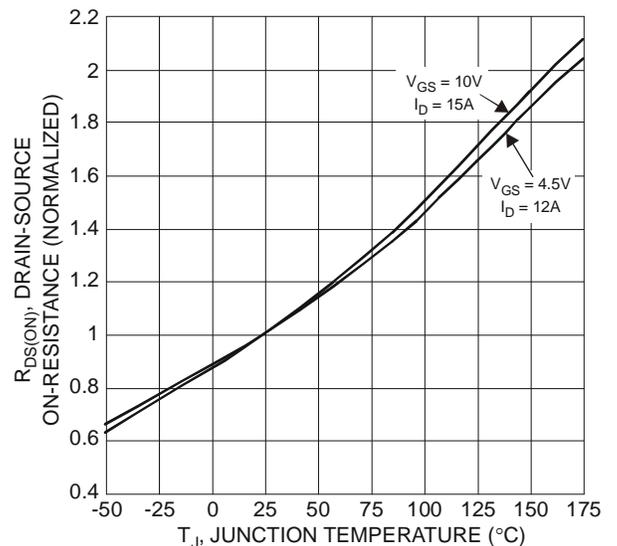


Figure 6 On-Resistance Variation with Temperature

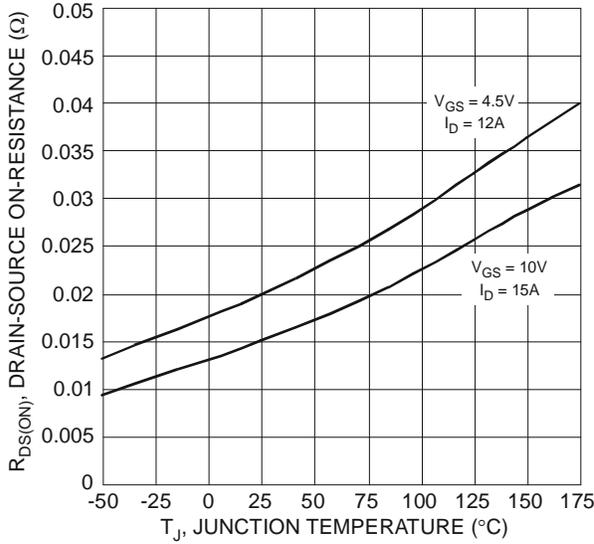


Figure 7 On-Resistance Variation with Temperature

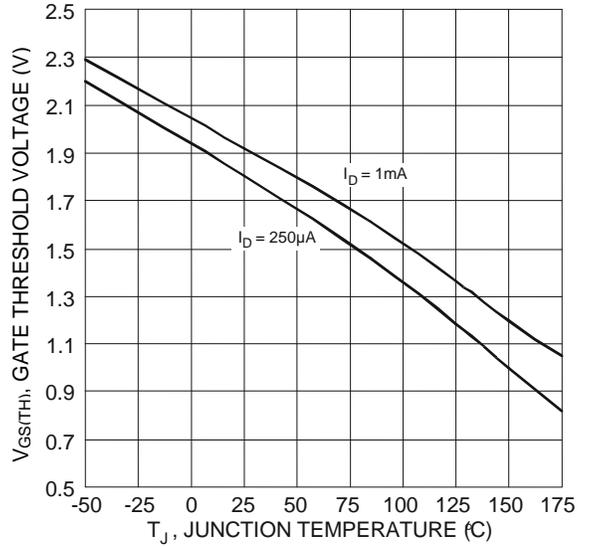


Figure 8 Gate Threshold Variation vs. Junction Temperature

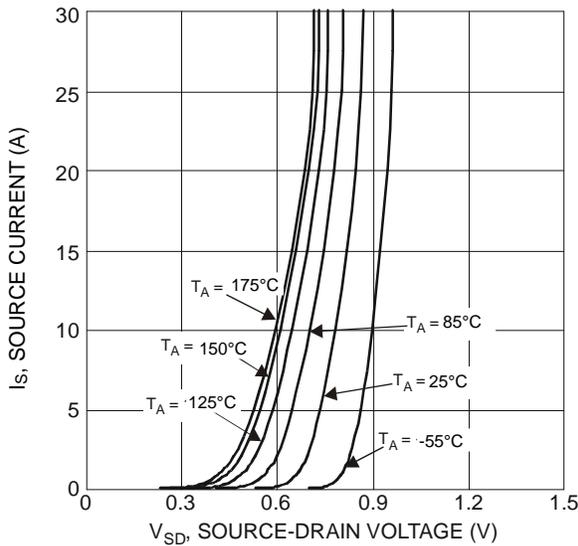


Figure 9 Diode Forward Voltage vs. Current

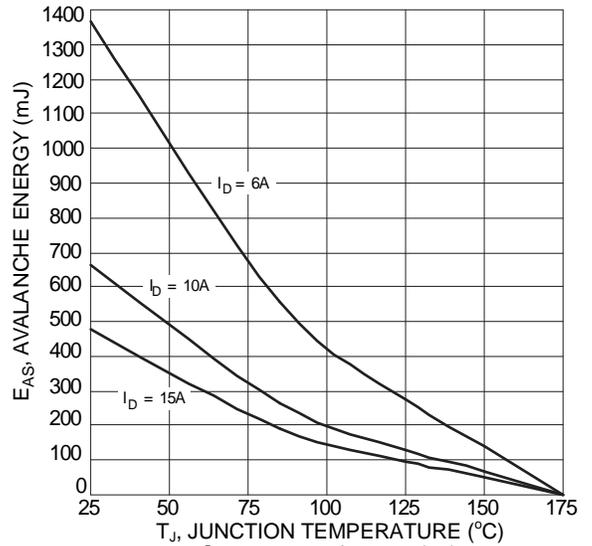


Figure 10 Avalanche Energy

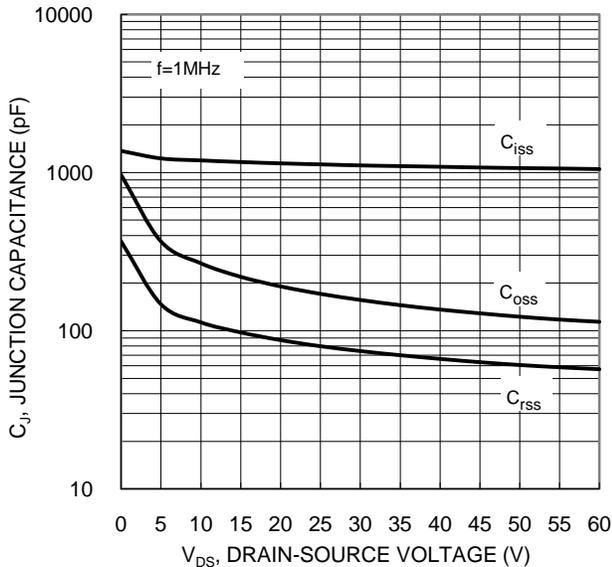


Figure 11 Typical Junction Capacitance

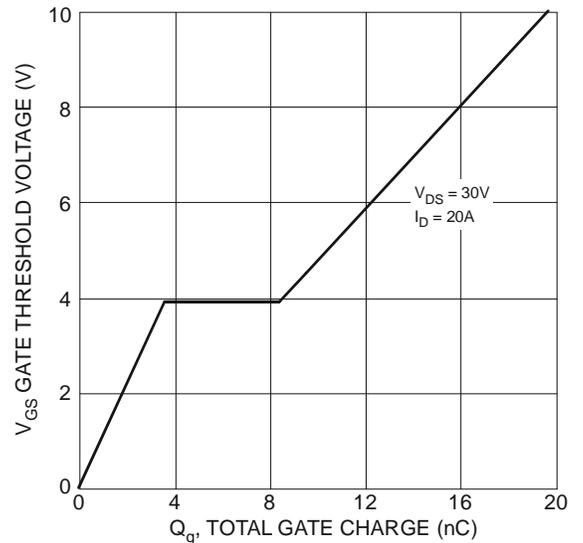


Figure 12 Gate Charge

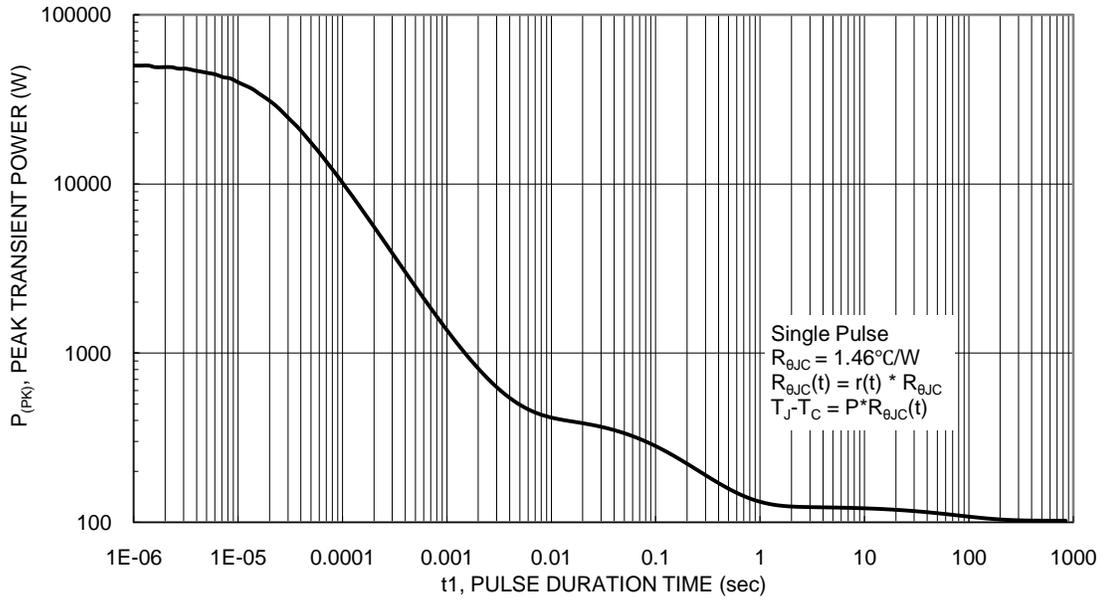


Figure 13 Single Pulse Maximum Power Dissipation

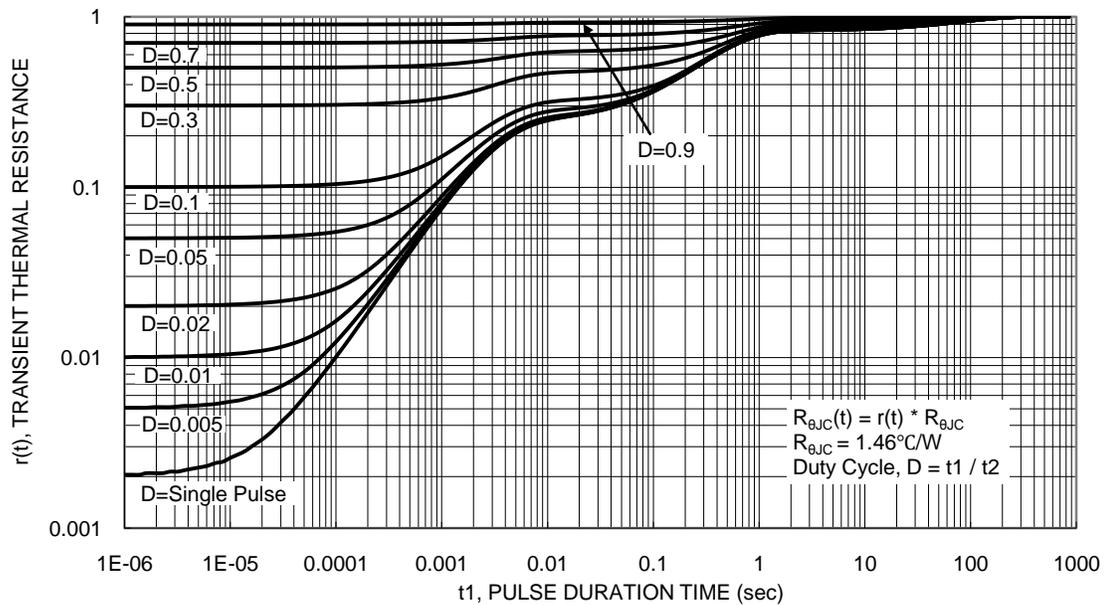
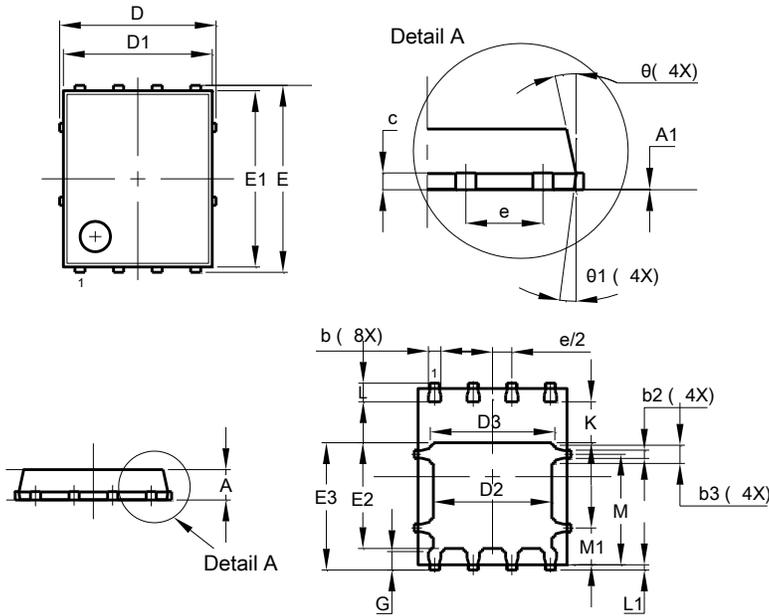


Figure 14 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**

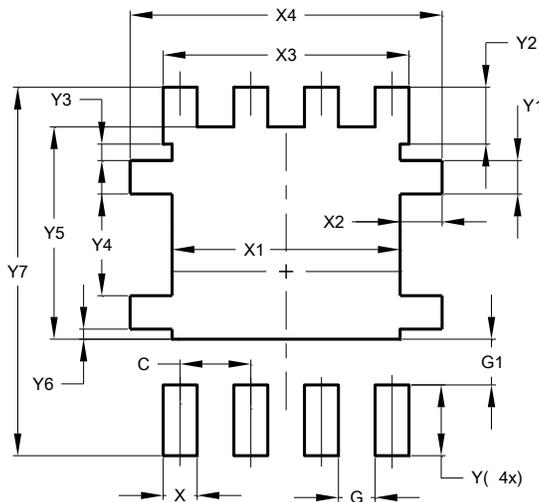


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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